762um×762um Silicon PD Chip datasheet

P/N ：WS9J-10B

Application

Si NIP photodiode chips.

Structure

Planar type：NIP diode

Electrodes ：

Top side（Cathode）: Al

Backside（Anode） : Au Alloy

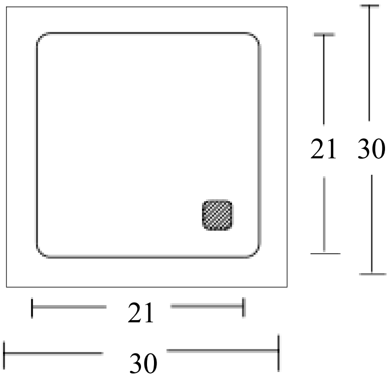
DIMENSIONS

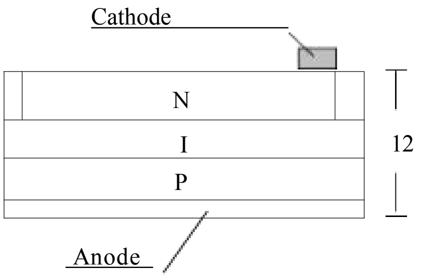
Conditions	Min.	Typ.	Max.	Unit
Active	21 × 21 (± 1.0)			mil
Chip width	30 × 30 （ ± 1.5 ）			mil
Chip length	30 × 30 (± 1.5 ）			mil
Chip height	12 （ ±1.0 ）			mil
Pad N(Cathode)	4.3 × 4.3			mil
Pad P(Anode)	4.3 × 4.3			mil

Electro-Optical Characteristics（ @ Ta＝25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF＝10mA, H＝0	0.5		1.3	V
Reverse Voltage	VBR	IR＝100μA, H＝0	35			V
Reverse Dark Current	ID	VR＝10V, H＝0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR＝3V, F＝1 MHz		9		pF

Unit ：mil





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